

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

TIG064E8 - N-Channel IGBT

N-Channel IGBT Light-Controlling Flash Applications

· Built-in Gate-to-Emitter protection diode

• Low voltage drive (2.5V)

dv / dt guarantee*

Features

- · Low-saturation voltage
- Enhansment type
- Mounting Height 0.9mm, Mounting Area 8.12mm²
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|--------------------------------------|-----------------------|--|-------------|------|
| Collector-to-Emitter Voltage | VCES | | 400 | V |
| Gate-to-Emitter Voltage (DC) | VGES | | ±4 | V |
| Gate-to-Emitter Voltage (Pulse) | VGES | PW≤1ms | ±5 | V |
| Collector Current (Pulse) | ICP | V _{GE} =2.5V, C _M =100μF | 150 | A |
| Maximum Collector-to-Emitter dv / dt | dV _{CE} / dt | V _{CE} ≤320V, starting Tch=25°C | 400 | V/μs |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -40 to +150 | °C |

* : Concerning dv / dt (slope of Collector Voltage at the time of Turn-OFF), dv / dt > 400V / μ s will be 100% screen-detected in the circuit shown as Fig. 1.

Package Dimensions

unit : mm (typ) 7011A-004



Product & Package Information

- Package : ECH8
- JEITA, JEDEC
- Minimum Packing Quantity : 3000 pcs./reel

: -

Packing Type: TL





Marking

Electrical Connection



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|---|-----------------------|--|-----|-------|-----|----|--|
| Parameter | Symbol | Conditions | min | typ | max | | |
| Collector-to-Emitter Breakdown Voltage | V(BR)CES | I _C =2mA, V _{GE} =0V | 400 | | | V | |
| Collector-to-Emitter Cutoff Current | ICES | V _{CE} =320V, V _{GE} =0V | | | 10 | μΑ | |
| Gate-to-Emitter Leakage Current | IGES | V _{GE} =±4V, V _{CE} =0V | | | ±10 | μA | |
| Gate-to-Emitter Threshold Voltage | V _{GE} (off) | V _{CE} =10V, I _C =1mA | 0.4 | | 0.9 | V | |
| Collector-to-Emitter Saturation Voltage | V _{CE} (sat) | IC=100A, VGE=2.5V | | 4.2 | 7 | V | |
| Input Capacitance | Cies | | | 3100 | | pF | |
| Output Capacitance | Coes | V _{CE} =10V, f=1MHz | | 30 | | pF | |
| Reverse Transfer Capacitance | Cres | | | 23 | | pF | |

Electrical Characteristics at Ta=25°C

Fig.1 Large Current R Load Switching Circuit



Note1. Gate Series Resistance $R_G \ge 160\Omega$ is recommended for protection purpose at the time of turn OFF. However, if $dv / dt \le 400V / \mu s$ is satisfied at customer's actual set evaluation, $R_G < 160\Omega$ can also be used.

Note2. The collector voltage gradient dv / dt must be smaller than 400V / µs to protect the device when it is turned off.

Ordering Information

| 0 | | | | | |
|---------------|----------------|----------------|--------------------------|--|--|
| Device | Device Package | | memo | | |
| TIG064E8-TL-H | ECH8 | 3,000pcs./reel | Pb Free and Halogen Free | | |











Embossed Taping Specification TIG064E8-TL-H

1. Packing Format

| Package Name | Carrier Tape | Maximum Number of devices contained (pcs) | | | Packing format | | | |
|--------------|---|--|------------------------|---|--|--|------------------------------------|---|
| | Туре | Reel | Inner box | Outer box | Inr | ner B(| OX (C−1) | Outer BOX (A-7) |
| ECH8 | СРНб | 3,000 | 15,000 | 90,000 | 5 ree | ls conta | lined | 6 inner boxes contained |
| | | | | | Dimen | ısions:r | nm (extern | nal) Dimensions:mm (external) |
| | | | | | 18 | 3×72 | 2 × 1 8 5 | 5 440×195×210 |
| Packing met | hod Type LOT Quan Orig Reel la | No. No. tity in | $\frac{\text{Reel}}{}$ | L abel,] (u: (u: (u: (u: (u: (u: (u: (u: (u: (u: | I O inner I n i t : m 5 9 0000000 0000000 0000000 0000000 0000000 0000000 00000000 000000000 00000000 00000000 00000000 00000000000 000000000000 00000000000000 000000000000000000000000000000000000 | <u></u> <u></u> <u></u> <u></u> <u></u> <u></u> <u></u> <u></u> <u></u> <u></u> | ion shows 1 is lead TA Phase | 5 440×195×210 atter box label is a label at the time of factory shipmen e form of a label may change in physical stribution process. 108 ************************************ |
| | | | | LEAD FRI | EE 4 | JEITA | A Phase | 3 |

2. Taping configuration

2-1. Carrier tape size (unit:mm)





Those with pin 1 index on the feed hole side·····TL

Outline Drawing TIG064E8-TL-H



Land Pattern Example



Note : TIG064E8 has protection diode between gate and emitter but handling it requires sufficient care to be taken.

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